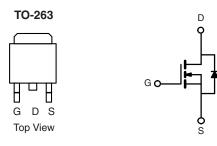


# Automotive N-Channel 330 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	330	
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = 10 V	0.160	
I <sub>D</sub> (A)	31	
Configuration	Single	



N-Channel MOSFET

#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % Rg and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM18N33-160H-GE3

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	i)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	330		
Gate-Source Voltage		V <sub>GS</sub> ± 30		V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	31		
	T <sub>C</sub> = 125 °C		18		
Continuous Source Current (Diode Conduction) <sup>a</sup>		IS	120	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	65		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	16		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	12	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P	375	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125		
Operating Junction and Storage Temperature	e Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
unction-to-Case (Drain)		R <sub>thJC</sub>	0.4	0/10	

Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR-4 material).

## SQM18N33-160H



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		330	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.8	5.0		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 30 V$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = 330 V	-	-	1		
	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 330 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 330 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.130	0.160	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.348		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.467		
Forward Transconductanceb	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	41	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		/ <sub>GS</sub> = 0 V V <sub>DS</sub> = 75 V, f = 1 MHz	-	3700	4625	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	140	210		
Reverse Transfer Capacitance	C <sub>rss</sub>	1   [		-	60	90		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = 175 V, I <sub>D</sub> = 18 A	-	71	105	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$		-	18	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	22	-		
Gate Resistance	Rg	f = 1 MHz		0.40	0.97	1.50	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	18	27		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 175 \text{ V}, \ R_{\text{L}} = 9.7 \ \Omega \\ I_{\text{D}} \cong 18 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	35	52	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	27	41		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	65	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 18 A, V <sub>GS</sub> = 0		-	1.1	1.5	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

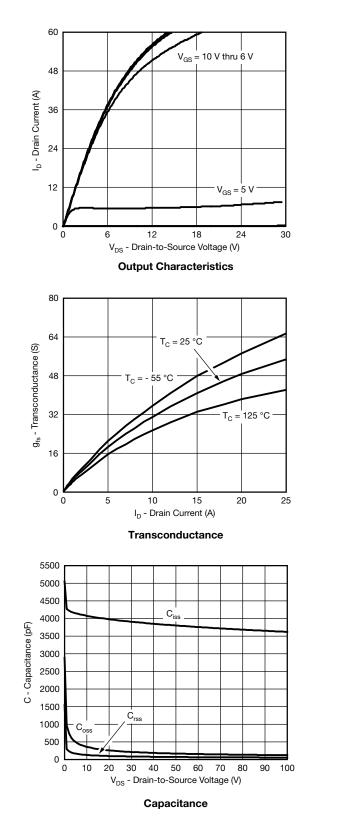
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

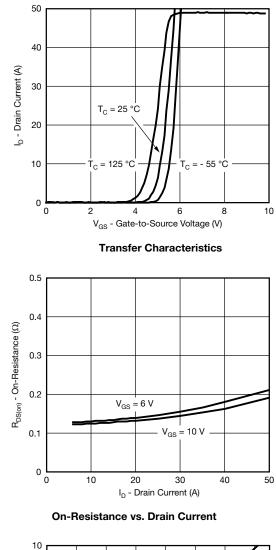


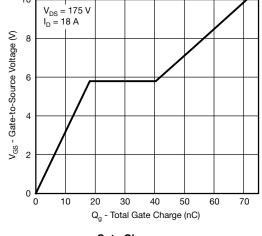
## SQM18N33-160H

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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





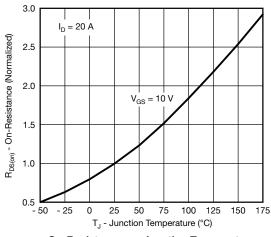


Gate Charge

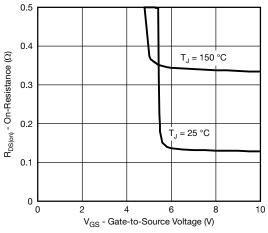
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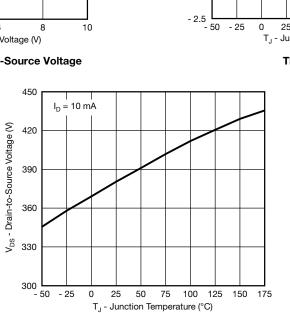
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



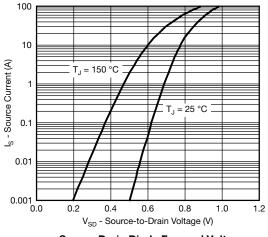
**On-Resistance vs. Junction Temperature** 



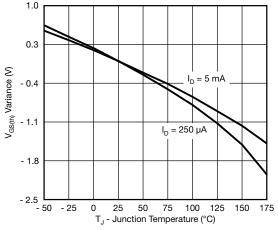
**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage

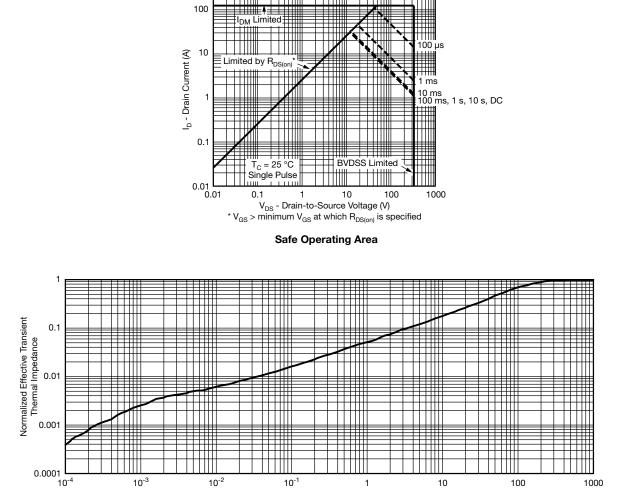


**Threshold Voltage** 

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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

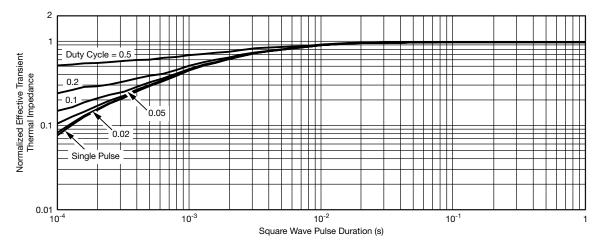


Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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